



**ALPHA & OMEGA**  
SEMICONDUCTOR

**AOT14N50/AOB14N50/AOTF14N50**  
**500V, 14A N-Channel MOSFET**

### General Description

The AOT14N50 &AOB14N50 & AOTF14N50 have been fabricated using an advanced high voltage MOSFET process that is designed to deliver high levels of performance and robustness in popular AC-DC applications.By providing low  $R_{DS(on)}$ ,  $C_{iss}$  and  $C_{rss}$  along with guaranteed avalanche capability these parts can be adopted quickly into new and existing offline power supply designs.

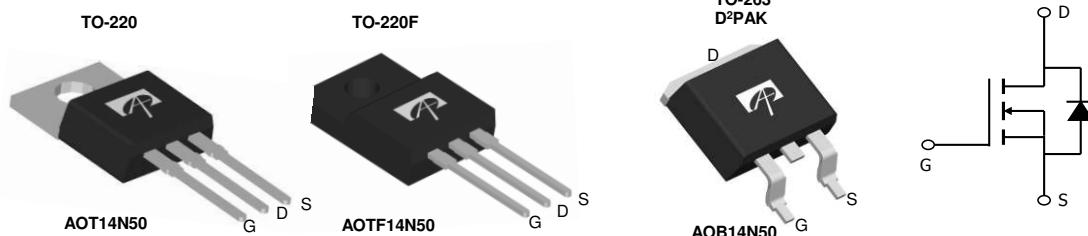
### Product Summary

$V_{DS}$	600V@150°C
$I_D$ (at $V_{GS}=10V$ )	14A
$R_{DS(ON)}$ (at $V_{GS}=10V$ )	< 0.38Ω

100% UIS Tested  
100%  $R_g$  Tested



Top View



### Absolute Maximum Ratings $T_A=25^\circ C$ unless otherwise noted

Parameter	Symbol	AOT14N50/AOB14N50	AOTF14N50	Units
Drain-Source Voltage	$V_{DS}$	500		V
Gate-Source Voltage	$V_{GS}$	$\pm 30$		V
Continuous Drain Current	$I_D$	14	14*	A
$T_c=100^\circ C$		11	11*	
Pulsed Drain Current <sup>C</sup>	$I_{DM}$	56		
Avalanche Current <sup>C</sup>	$I_{AR}$	6		A
Repetitive avalanche energy <sup>C</sup>	$E_{AR}$	540		mJ
Single pulsed avalanche energy <sup>G</sup>	$E_{AS}$	1080		mJ
Peak diode recovery dv/dt	dv/dt	5		V/ns
$T_c=25^\circ C$	$P_D$	278	50	W
Power Dissipation <sup>B</sup> Derate above $25^\circ C$		2.2	0.4	$W/^\circ C$
Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 to 150		$^\circ C$
Maximum lead temperature for soldering purpose, 1/8" from case for 5 seconds	$T_L$	300		$^\circ C$
<b>Thermal Characteristics</b>				
Parameter	Symbol	AOT14N50/AOB14N50	AOTF14N50	Units
Maximum Junction-to-Ambient <sup>A,D</sup>	$R_{\theta JA}$	65	65	$^\circ C/W$
Maximum Case-to-sink <sup>A</sup>	$R_{\theta CS}$	0.5	--	$^\circ C/W$
Maximum Junction-to-Case	$R_{\theta JC}$	0.45	2.5	$^\circ C/W$

\* Drain current limited by maximum junction temperature.

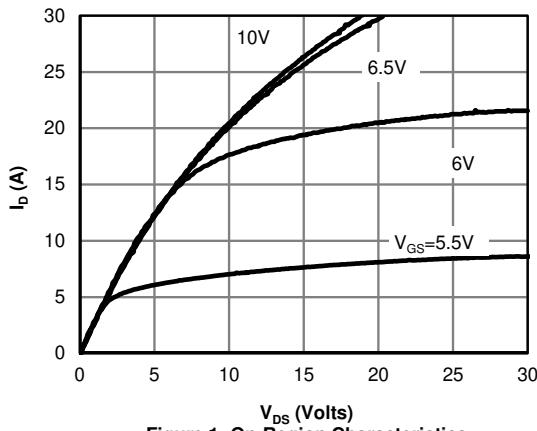
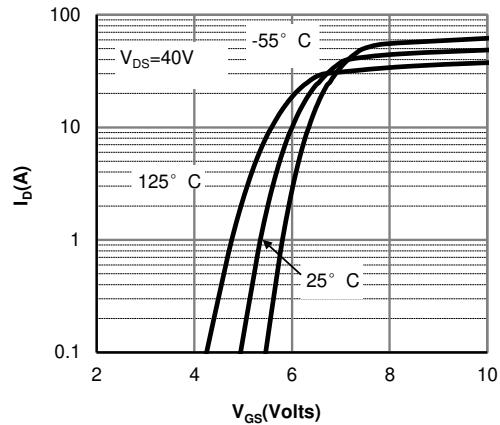
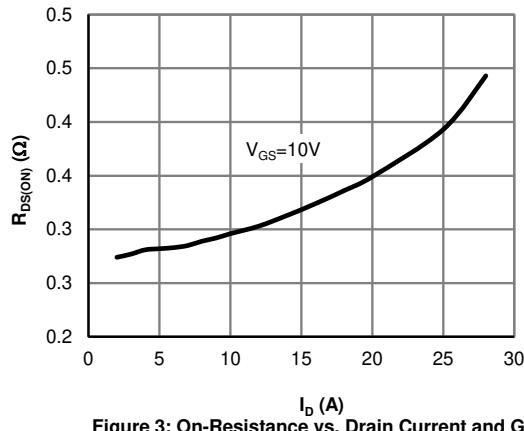
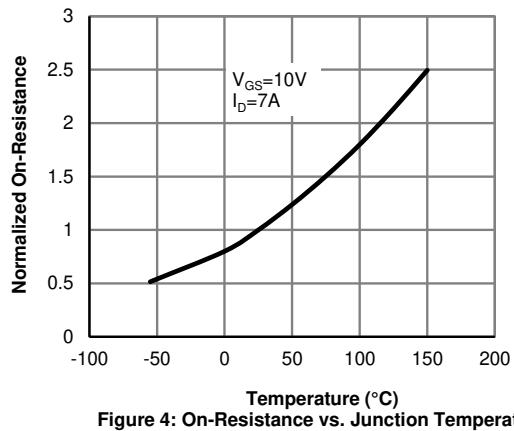
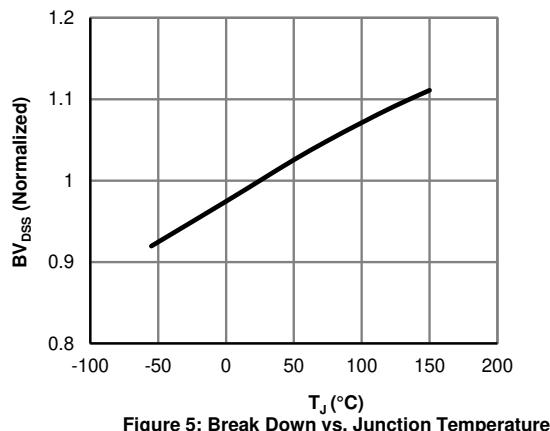
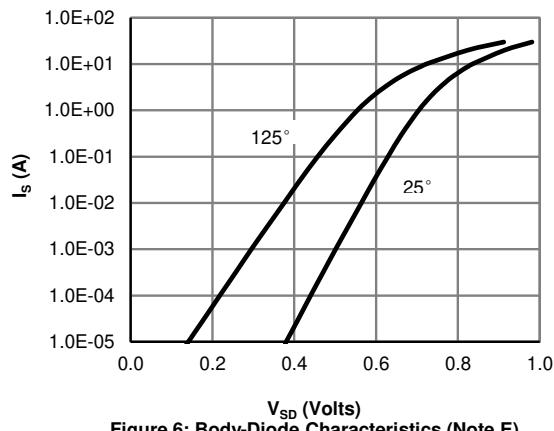
**Electrical Characteristics ( $T_J=25^\circ\text{C}$  unless otherwise noted)**

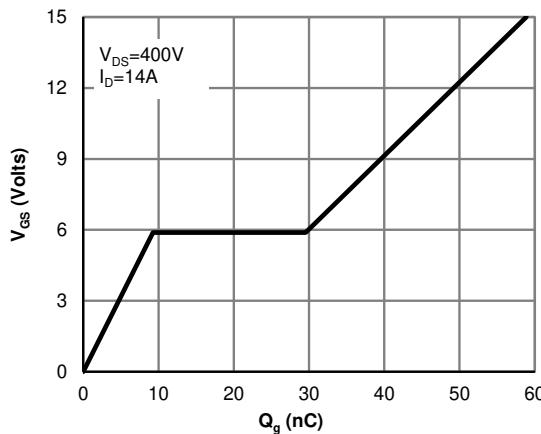
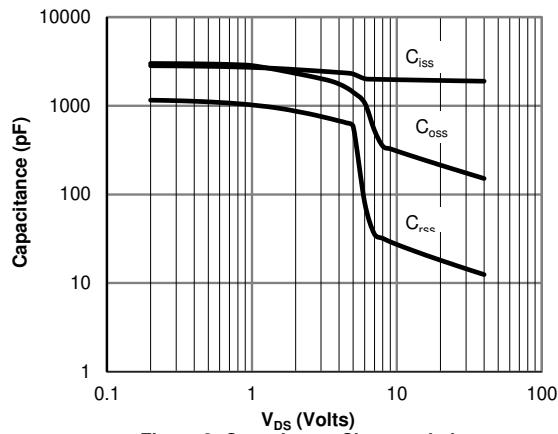
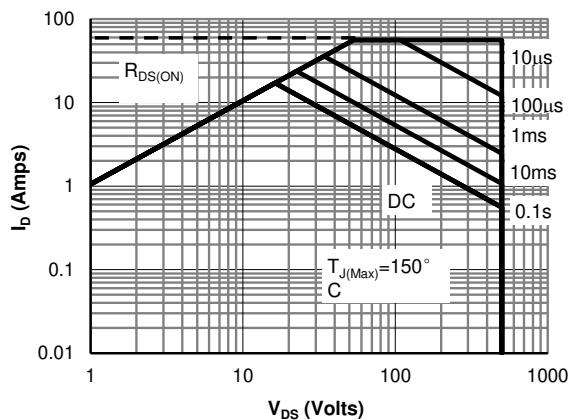
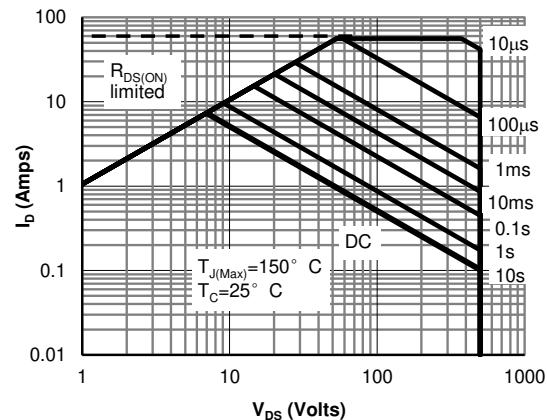
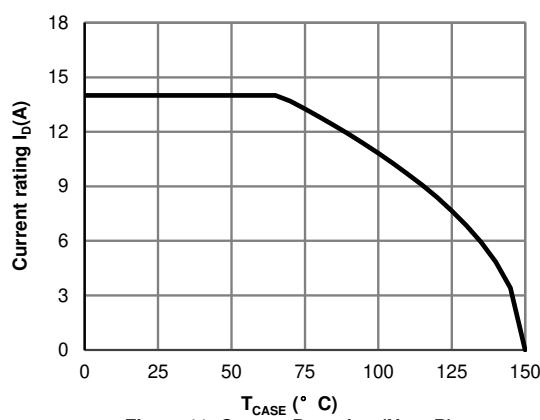
Symbol	Parameter	Conditions	Min	Typ	Max	Units
<b>STATIC PARAMETERS</b>						
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	I <sub>D</sub> =250μA, V <sub>GS</sub> =0V, T <sub>J</sub> =25°C	500			V
		I <sub>D</sub> =250μA, V <sub>GS</sub> =0V, T <sub>J</sub> =150°C		600		
BV <sub>DSS</sub> /ΔT <sub>J</sub>	Breakdown Voltage Temperature Coefficient	I <sub>D</sub> =250μA, V <sub>GS</sub> =0V		0.5		V/°C
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> =500V, V <sub>GS</sub> =0V		1		μA
		V <sub>DS</sub> =400V, T <sub>J</sub> =125°C		10		
I <sub>GSS</sub>	Gate-Body leakage current	V <sub>DS</sub> =0V, V <sub>GS</sub> =±30V			±100	nA
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> =5V I <sub>D</sub> =250μA	3.3	4.2	4.5	V
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance	V <sub>GS</sub> =10V, I <sub>D</sub> =7A		0.29	0.38	Ω
g <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> =40V, I <sub>D</sub> =7A		20		S
V <sub>SD</sub>	Diode Forward Voltage	I <sub>S</sub> =1A, V <sub>GS</sub> =0V		0.71	1	V
I <sub>S</sub>	Maximum Body-Diode Continuous Current				14	A
I <sub>SM</sub>	Maximum Body-Diode Pulsed Current				56	A
<b>DYNAMIC PARAMETERS</b>						
C <sub>iss</sub>	Input Capacitance	V <sub>GS</sub> =0V, V <sub>DS</sub> =25V, f=1MHz	1531	1914	2297	pF
C <sub>oss</sub>	Output Capacitance		153	191	229	pF
C <sub>rss</sub>	Reverse Transfer Capacitance		11	16	20	pF
R <sub>g</sub>	Gate resistance	V <sub>GS</sub> =0V, V <sub>DS</sub> =0V, f=1MHz	1.75	3.5	5.3	Ω
<b>SWITCHING PARAMETERS</b>						
Q <sub>g</sub>	Total Gate Charge	V <sub>GS</sub> =10V, V <sub>DS</sub> =400V, I <sub>D</sub> =14A		42.8	51	nC
	Gate Source Charge			9.3	11	nC
	Gate Drain Charge			20.3	24	nC
t <sub>D(on)</sub>	Turn-On Delay Time	V <sub>GS</sub> =10V, V <sub>DS</sub> =250V, I <sub>D</sub> =14A, R <sub>G</sub> =25Ω		44	53	ns
t <sub>r</sub>	Turn-On Rise Time			84	101	ns
t <sub>D(off)</sub>	Turn-Off Delay Time			92	110	ns
t <sub>f</sub>	Turn-Off Fall Time			50	60	ns
t <sub>rr</sub>	Body Diode Reverse Recovery Time	I <sub>F</sub> =14A, dI/dt=100A/μs, V <sub>DS</sub> =100V		289	347	ns
Q <sub>rr</sub>	Body Diode Reverse Recovery Charge	I <sub>F</sub> =14A, dI/dt=100A/μs, V <sub>DS</sub> =100V		4.93	6	μC

- A. The value of R<sub>θJA</sub> is measured with the device in a still air environment with T<sub>A</sub>=25°C.  
 B. The power dissipation P<sub>D</sub> is based on T<sub>J(MAX)=150°C</sub>, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.  
 C. Repetitive rating, pulse width limited by junction temperature T<sub>J(MAX)=150°C</sub>. Ratings are based on low frequency and duty cycles to keep initial T<sub>J</sub>=25°C.  
 D. The R<sub>θJA</sub> is the sum of the thermal impedance from junction to case R<sub>θJC</sub> and case to ambient.  
 E. The static characteristics in Figures 1 to 6 are obtained using <300 μs pulses, duty cycle 0.5% max.  
 F. These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of T<sub>J(MAX)=150°C</sub>. The SOA curve provides a single pulse rating.  
 G. L=60mH, I<sub>AS</sub>=6A, V<sub>DD</sub>=150V, R<sub>G</sub>=25Ω, Starting T<sub>J</sub>=25°C

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**TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS**

**Figure 1: On-Region Characteristics**

**Figure 2: Transfer Characteristics**

**Figure 3: On-Resistance vs. Drain Current and Gate Voltage**

**Figure 4: On-Resistance vs. Junction Temperature**

**Figure 5: Break Down vs. Junction Temperature**

**Figure 6: Body-Diode Characteristics (Note E)**

**TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS**

**Figure 7: Gate-Charge Characteristics**

**Figure 8: Capacitance Characteristics**

**Figure 9: Maximum Forward Biased Safe Operating Area for AOT14N50/AOB14N50 (Note F)**

**Figure 10: Maximum Forward Biased Safe Operating Area for AOTF14N50 (Note F)**

**Figure 11: Current De-rating (Note B)**

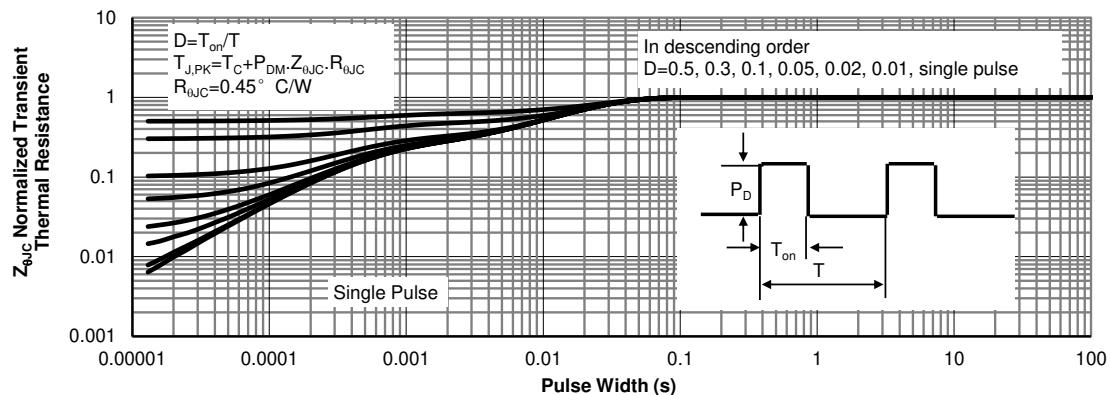
**TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS**


Figure 12: Normalized Maximum Transient Thermal Impedance for AOT14N50/AOB14N50 (Note F)

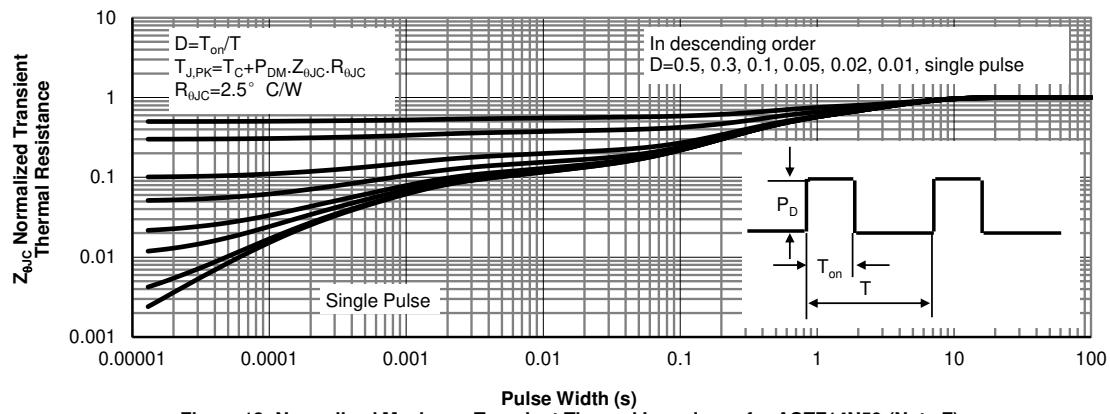
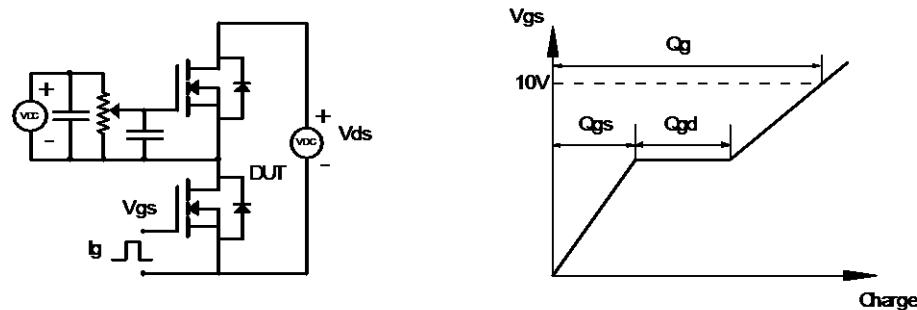
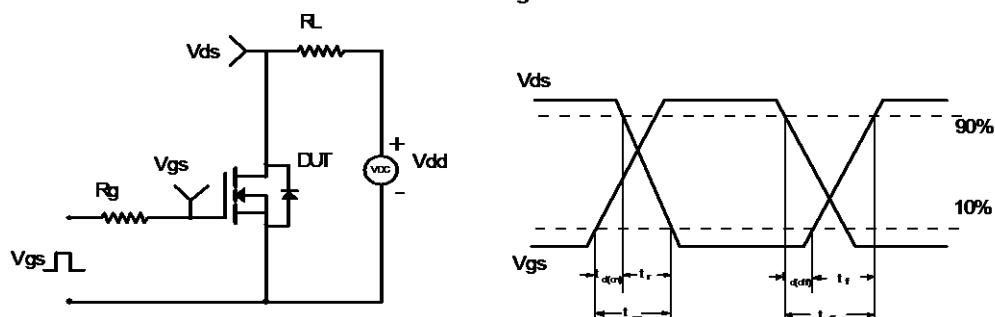
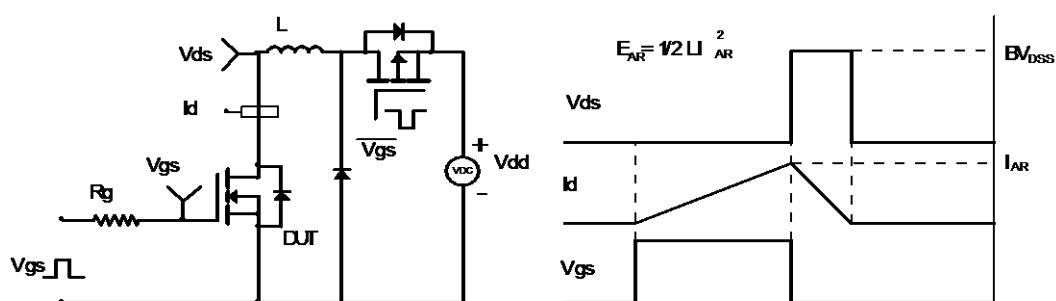


Figure 13: Normalized Maximum Transient Thermal Impedance for AOTF14N50 (Note F)

**Gate Charge Test Circuit & Waveform**

**Resistive Switching Test Circuit & Waveforms**

**Unclamped Inductive Switching (UIS) Test Circuit & Waveforms**

**Diode Recovery Test Circuit & Waveforms**
